

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

Claims 1-12 (Cancelled).

13. (New) An interconnecting structure comprising:
a first dielectric film;
a first wiring conductor in the first dielectric film;
a second dielectric film on the first wiring conductor and on the first dielectric film;
a third dielectric film on the second dielectric film;
a via in the second dielectric film and a first portion of the third dielectric film, the via being connected to the first wiring conductor;
a second wiring conductor in a second portion of the third dielectric film, on the via, the second wiring conductor being connected to the via; and
a dummy conductor in the second and third dielectric films, the dummy conductor contacting the first dielectric film.

14. (New) The interconnecting structure according to claim 13, wherein the second dielectric film includes nitrogen atoms.

15. (New) The interconnecting structure according to claim 13, wherein the first dielectric film includes nitrogen atoms.

16. (New) The interconnecting structure according to claim 13, wherein the first wiring conductor is covered with the second dielectric film.

17. (New) The interconnecting structure according to claim 13, wherein the second dielectric film is thinner than the third dielectric film.

18. (New) The interconnecting structure according to claim 13, wherein the dummy conductor is not connected to any wiring conductor.

19. (New) An interconnecting structure comprising:
a semiconductor substrate;
a first dielectric film supported by the semiconductor substrate;
a first wiring conductor in the first dielectric film;
a second dielectric film on the first wiring conductor and on the first dielectric film;
a third dielectric film on the second dielectric film;
a second wiring conductor in the second and third dielectric films, the second wiring conductor being connected to the first wiring conductor; and
a dummy conductor in the second and third dielectric films, the dummy conductor contacting the first dielectric film.

20. (New) The interconnecting structure according to claim 19, wherein the second dielectric film includes nitrogen atoms.

21. (New) The interconnecting structure according to claim 19, wherein the first dielectric film includes nitrogen atoms.

22. (New) The semiconductor device according to claim 19, wherein the second wiring conductor has a wiring portion and a via portion, and the via portion connects the first wiring conductor to the wiring portion.

23. (New) The interconnecting structure according to claim 19, wherein the first wiring conductor is covered with the second dielectric film.

24. (New) The interconnecting structure according to claim 19, wherein the second dielectric film is thinner than the third dielectric film.

25. (New) The interconnecting structure according to claim 19, wherein the dummy conductor is not connected to any wiring conductor.

26. (New) An interconnecting structure comprising:
a semiconductor substrate;
a first dielectric film supported by the semiconductor substrate;
a first wiring conductor in the first dielectric film;
a second dielectric film on the first wiring conductor and on the first dielectric film;
a third dielectric film on the second dielectric film;
a second wiring conductor in the second and third dielectric films, the second wiring conductor being connected to the first wiring conductor; and
a plurality of dummy conductors in the second and third dielectric films, each of the dummy conductors contacting the first dielectric film, wherein the plurality of dummy conductors are arranged around the second wiring conductor.

27. (New) The interconnecting structure according to claim 26, wherein the second dielectric film includes nitrogen atoms.

28. (New) The interconnecting structure according to claim 26, wherein the first dielectric film includes nitrogen atoms.

29. (New) The interconnecting structure according to claim 26, wherein the first wiring conductor is covered with the second dielectric film.

30. (New) The interconnecting structure according to claim 26, wherein the second dielectric film is thinner than the third dielectric film.

31. (New) The interconnecting structure according to claim 26, wherein the dummy conductor is not connected to any wiring conductor.